

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method for anisotropically etching a Cu-containing layer comprising the steps of:

providing a Cu-containing layer overlying a substrate;
introducing a directional beam of neutral oxygen atoms having a ~~high~~ kinetic energy between 10 eV and 1 eV;
oxidizing the Cu-containing layer by exposure to the beam of oxygen atoms;
introducing a reagent capable of forming volatile etch products when reacted with the oxidized Cu-containing layer;
removing the etch products from the Cu-containing layer.

Claim 2 (Original): The method according to claim 1, wherein the reagent comprises a β -diketone gas.

Claim 3 (Original): The method according to claim 2, wherein the β -diketone gas comprises at least one of acacH, tfacH, and hfacH.

Claim 4 (Original): The method according to claim 1, further comprising introducing an inert gas.

Claim 5 (Original): The method according to claim 4, wherein the inert gas comprises at least one of argon, helium, xenon, and nitrogen.

Claim 6 (Original): The method according to claim 1, wherein the substrate is maintained at a temperature below 200°C.

Claim 7 (Original): The method according to claim 1, wherein the substrate is maintained at a temperature below 150°C.

Claim 8 (Original): The method according to claim 1, wherein the substrate is maintained at a temperature below 100°C.

Claims 9-21 (Canceled).